

## GaN Wideband 15 W Pulsed Transistor in Plastic Package DC - 3.5 GHz

Rev. V3

### Features

- GaN on SiC D-Mode Transistor Technology
- Unmatched, Ideal for Pulsed Applications
- 50 V Typical Bias, Class AB
- Common-Source Configuration
- Thermally-Enhanced 3 x 6 mm 14-Lead DFN
- MTTF = 600 years ( $T_J < 200^\circ\text{C}$ )
- Halogen-Free “Green” Mold Compound
- RoHS\* Compliant and 260°C Reflow Compatible
- MSL-1

### Description

The MAGX-000035-01500P is a GaN on SiC unmatched power device offering the widest RF frequency capability, most reliable high voltage operation, lowest overall power transistor size, cost and weight in a “TRUE SMT” plastic-packaging technology.

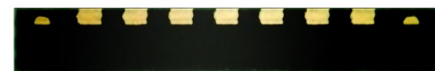
Use of an internal stress buffer technology allows reliable operation at junction temperatures up to 200°C. The small package size and excellent RF performance make it an ideal replacement for costly flanged or metal-backed module components.

### Ordering Information<sup>1,2</sup>

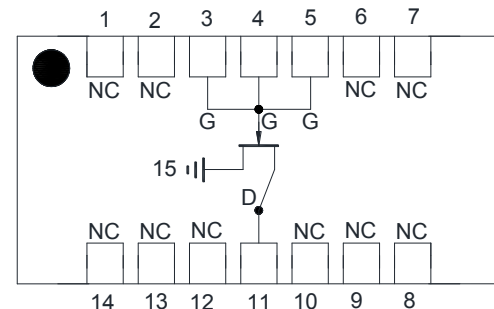
Part Number	Package
MAGX-000035-01500P	Bulk Packaging
MAGX-000035-0150TP	250 Piece Reel
MAGX-000035-PB1PPR	Sample Board

1. Reference Application Note M513 for reel size information.
2. When ordering sample evaluation boards, choose a standard frequency range indicated on page 4 or specify a desired custom range. Custom requests may increase lead times.

\* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.



### Functional Schematic



### Pin Configuration<sup>3</sup>

Pin No.	Function	Pin No.	Function
1	No Connection	8	No Connection
2	No Connection	9	No Connection
3	$V_{GG}/RF_{IN}$	10	No Connection
4	$V_{GG}/RF_{IN}$	11	$V_{DD}/RF_{OUT}$
5	$V_{GG}/RF_{IN}$	12	No Connection
6	No Connection	13	No Connection
7	No Connection	14	No Connection
		15	Paddle <sup>4</sup>

3. MACOM recommends connecting unused package pins to ground.
4. The exposed pad centered on the package bottom must be connected to RF and DC ground.

**GaN Wideband 15 W Pulsed Transistor in Plastic Package**  
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Rev. V3

**Typical Performance<sup>5</sup>:  $V_{DD} = 50\text{ V}$ ,  $I_{DQ} = 35\text{ mA}$ ,  $T_A = 25^\circ\text{C}$** 

Parameter	30 MHz	1 GHz	2.5 GHz	3.5 GHz	Units
Gain	25	23	17	14	dB
Saturated Power ( $P_{SAT}$ )	18	16.5	15	14	W
Power Gain at $P_{SAT}$	22	18	14	11	dB
PAE @ $P_{SAT}$	75	68	60	55	%

5. Typical RF performance measured in M/A-COM Technology Solutions RF evaluation boards. See recommended tuning solutions on page 4.

**Electrical Specifications: Freq. = 1.6 GHz,  $T_A = 25^\circ\text{C}$ ,  $V_{DD} = +50\text{ V}$ ,  $Z_0 = 50\ \Omega$** 

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
<b>RF FUNCTIONAL TESTS</b>						
CW Output Power (P2.5 dB)	$V_{DD} = 36\text{ V}$ , $I_{DQ} = 35\text{ mA}$	$P_{OUT}$	-	7	-	W
Pulsed Output Power (P2.5 dB) 1 ms and 10% Duty Cycle	$V_{DD} = 50\text{ V}$ , $I_{DQ} = 35\text{ mA}$	$P_{OUT}$	12.5	17	-	W
Pulsed Power Gain (P2.5 dB)	$V_{DD} = 50\text{ V}$ , $I_{DQ} = 35\text{ mA}$	$G_P$	17	19.5	-	dB
Pulsed Drain Efficiency (P2.5 dB)	$V_{DD} = 50\text{ V}$ , $I_{DQ} = 35\text{ mA}$	$\eta_D$	55	65	-	%
Load Mismatch Stability (P2.5 dB)	$V_{DD} = 50\text{ V}$ , $I_{DQ} = 35\text{ mA}$	VSWR-S	-	5:1	-	-
Load Mismatch Tolerance (P2.5 dB)	$V_{DD} = 50\text{ V}$ , $I_{DQ} = 35\text{ mA}$	VSWR-T	-	10:1	-	-

**Electrical Characteristics:  $T_A = 25^\circ\text{C}$** 

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
<b>DC CHARACTERISTICS</b>						
Drain-Source Leakage Current	$V_{GS} = -8\text{ V}$ , $V_{DS} = 175\text{ V}$	$I_{DS}$	-	-	1.0	mA
Gate Threshold Voltage	$V_{DS} = 5\text{ V}$ , $I_D = 2\text{ mA}$	$V_{GS(th)}$	-5	-3	-2	V
Forward Transconductance	$V_{DS} = 5\text{ V}$ , $I_D = 500\text{ mA}$	$G_M$	0.35	-	-	S
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$V_{DS} = 0\text{ V}$ , $V_{GS} = -8\text{ V}$ , $F = 1\text{ MHz}$	$C_{ISS}$	-	4.2	-	pF
Output Capacitance	$V_{DS} = 50\text{ V}$ , $V_{GS} = -8\text{ V}$ , $F = 1\text{ MHz}$	$C_{OSS}$	-	1.8	-	pF
Reverse Transfer Capacitance	$V_{DS} = 50\text{ V}$ , $V_{GS} = -8\text{ V}$ , $F = 1\text{ MHz}$	$C_{RSS}$	-	0.2	-	pF

**GaN Wideband 15 W Pulsed Transistor in Plastic Package**  
**DC - 3.5 GHz**

Rev. V3

**Absolute Maximum Ratings** <sup>6,7,8,9,10</sup>

Parameter	Absolute Max.
Input Power	$P_{OUT} - G_P + 2.5 \text{ dBm}$
Drain Supply Voltage, $V_{DD}$	+65 V
Gate Supply Voltage, $V_{GG}$	-8 V to 0 V
Supply Current, $I_{DD}$	800 mA
Power Dissipation, CW @ 85°C	13 W
Power Dissipation ( $P_{AVG}$ ), Pulsed @ 85°C	17 W
Junction Temperature <sup>11</sup>	200°C
Operating Temperature	-40°C to +95°C
Storage Temperature	-65°C to +150°C

6. Exceeding any one or combination of these limits may cause permanent damage to this device.  
7. M/A-COM Technology Solutions does not recommend sustained operation near these survivability limits.  
8. For saturated performance it is recommended that the sum of  $(3 * V_{DD} + \text{abs}(V_{GG})) \leq 175 \text{ V}$ .  
9. CW operation at  $V_{DD}$  voltages above 36 V is not recommended.  
10. Operating at nominal conditions with  $T_J \leq 200^\circ\text{C}$  will ensure  $\text{MTTF} > 1 \times 10^6$  hours. Junction temperature directly affects device MTTF and should be kept as low as possible to maximize lifetime.  
11. Junction Temperature ( $T_J$ ) =  $T_C + \Theta_{JC} * ((V * I) - (P_{OUT} - P_{IN}))$

Typical CW thermal resistance ( $\Theta_{JC}$ ) = 15.7°C/W

a) For  $T_C = 83^\circ\text{C}$ ,

$T_J = 200^\circ\text{C}$  @ 36 V, 398 mA,  $P_{OUT} = 7.2 \text{ W}$ ,  $P_{IN} = 0.22 \text{ W}$

Typical transient thermal resistances:

b) 300  $\mu\text{s}$  pulse, 10% duty cycle,  $\Theta_{JC} = 5.33^\circ\text{C/W}$

For  $T_C = 83^\circ\text{C}$ ,

$T_J = 170^\circ\text{C}$  @ 50 V, 603 mA,  $P_{OUT} = 14.3 \text{ W}$ ,  $P_{IN} = 0.41 \text{ W}$

c) 1 ms pulse, 10% duty cycle,  $\Theta_{JC} = 5.85^\circ\text{C/W}$

For  $T_C = 83^\circ\text{C}$ ,

$T_J = 172^\circ\text{C}$  @ 50 V, 576 mA,  $P_{OUT} = 14.0 \text{ W}$ ,  $P_{IN} = 0.41 \text{ W}$

d) 1 ms pulse, 20% duty cycle,  $\Theta_{JC} = 6.81^\circ\text{C/W}$

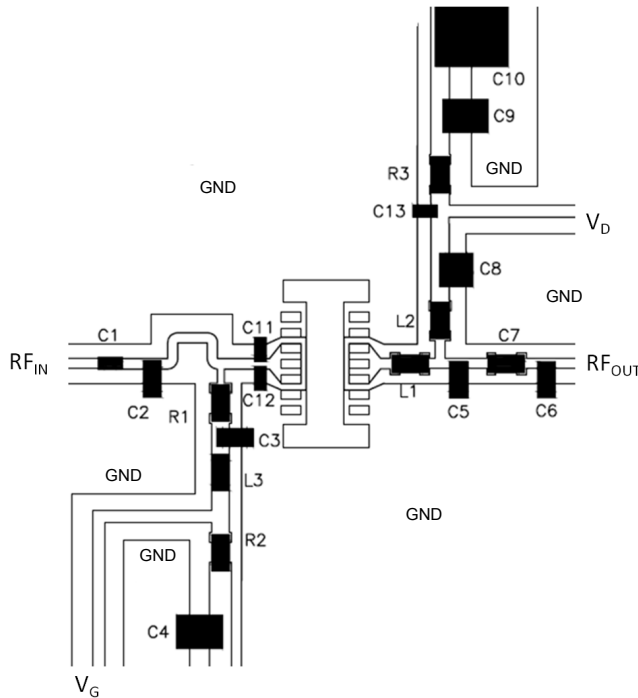
For  $T_C = 83^\circ\text{C}$ ,

$T_J = 186^\circ\text{C}$  @ 50 V, 570 mA,  $P_{OUT} = 13.8 \text{ W}$ ,  $P_{IN} = 0.41 \text{ W}$

## GaN Wideband 15 W Pulsed Transistor in Plastic Package DC - 3.5 GHz

Rev. V3

### Evaluation Board Details and Recommended Tuning Solutions



Parts measured on evaluation board (8-mils thick RO4003C). Electrical and thermal ground is provided using copper-filled via hole array (not pictured), and evaluation board is mounted to a metal plate.

Matching is provided using lumped elements as shown at left. Recommended tuning solutions for 3 frequency ranges are detailed in the parts list below.

### Bias Sequencing

#### Turning the device ON

1. Set  $V_G$  to the pinch-off ( $V_P$ ), typically -5 V.
2. Turn on  $V_D$  to nominal voltage (50 V).
3. Increase  $V_{GS}$  until the  $I_{DS}$  current is reached.
4. Apply RF power to desired level.

#### Turning the device OFF

1. Turn the RF power off.
2. Decrease  $V_G$  down to  $V_P$ .
3. Decrease  $V_D$  down to 0 V.
4. Turn off  $V_G$ .

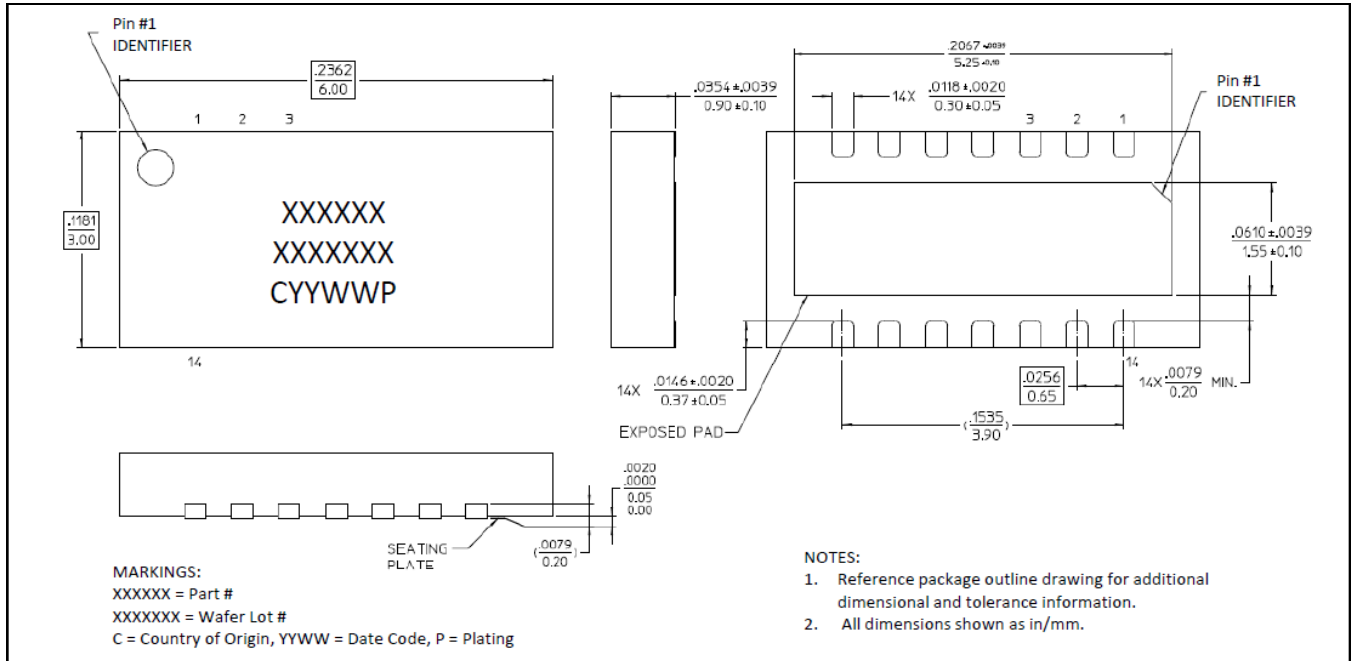
### Parts List (N/A = not applicable for this tuning solution)

Part	Frequency = 1.6 GHz	Frequency = 2.2 - 2.5 GHz	Frequency = 2.6 - 3.6 GHz
C1	0402 27 pF, $\pm 5\%$ , 200 V, ATC	0402 18 pF, $\pm 5\%$ , 200 V, ATC	0402 18 pF, $\pm 5\%$ , 200 V, ATC
C2	0603, 5.6 pF, $\pm 0.1$ pF, 250 V, ATC	0402, 2.2 pF, $\pm 0.1$ pF, 200 V, ATC	0402, 1.2 pF, $\pm 0.1$ pF, 200 V, ATC
C3	0603, 18 pF, $\pm 10\%$ , 250 V, ATC	N/A	N/A
C4	0805, 1000 pF, 100 V, 5%, AVX	0805, 1000 pF, 100 V, 5%, AVX	0805, 1000 pF, 100 V, 5%, AVX
C5	0505, 2.2 pF, $\pm 5\%$ , 250 V, ATC (Vertical)	0603, 0.8 pF, $\pm 0.1$ pF, 250 V, ATC	N/A
C6	N/A	0603, 1.5 pF, $\pm 0.1$ pF, 250 V, ATC	0402, 1.0 pF, $\pm 0.1$ pF, 200 V, ATC
C7	0505, 36 pF, $\pm 5\%$ , 250 V, ATC (Vertical)	0402 18 pF, $\pm 5\%$ , 200 V, ATC	0402 18 pF, $\pm 5\%$ , 200 V, ATC
C8	0505, 18 pF, $\pm 5\%$ , 250 V, ATC	0402 10 pF, $\pm 5\%$ , 200 V, ATC	N/A
C9	0805, 1000 pF, 100 V, 5%, AVX	0805, 1000 pF, 100 V, 5%, AVX	0805, 1000pF, 100V, 5%, AVX
C10	1210, 1 $\mu$ F, 100 V, 20%, ATC	1210, 1 $\mu$ F, 100 V, 20%, ATC	1210, 1 $\mu$ F, 100 V, 20%, ATC
C11	N/A	0402, 3.9 pF, $\pm 0.1$ pF, 200 V, ATC	0402, 2.0 pF, $\pm 0.1$ pF, 200 V, ATC
C12	N/A	0402, 3.9 pF, $\pm 0.1$ pF, 200 V, ATC	0402, 2.0 pF, $\pm 0.1$ pF, 200 V, ATC
C13	N/A	N/A	0402 10 pF, $\pm 5\%$ , 200 V, ATC
R1	12 $\Omega$ , 0603, 5%	200 $\Omega$ , 0603, 5%	100 $\Omega$ , 0603, 5%
R2	1.2 $\Omega$ , 0603, 5%	1.0 $\Omega$ , 0603, 5%	1.0 $\Omega$ , 0603, 5%
R3	1.2 $\Omega$ , 0603, 5%	9.1 $\Omega$ , 0603, 5%	9.1 $\Omega$ , 0603, 5%
L1	0603 HP, 5.1 nH, 5%	0402, 0.8 nH, 10%	Shorting tab
L2	0603 HP, 24 nH, 5%	0603, 1.8 nH, 10%	Shorting tab
L3	N/A	N/A	0603, 10nH, 10%

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Rev. V3

### Lead-Free 3x6 mm 14-Lead DFN<sup>†</sup>



<sup>†</sup> Reference Application Note S2083 for lead-free solder reflow recommendations.  
 Meets JEDEC moisture sensitivity level 1 requirements.  
 Plating is Ni/Pd/Au.

### Handling Procedures

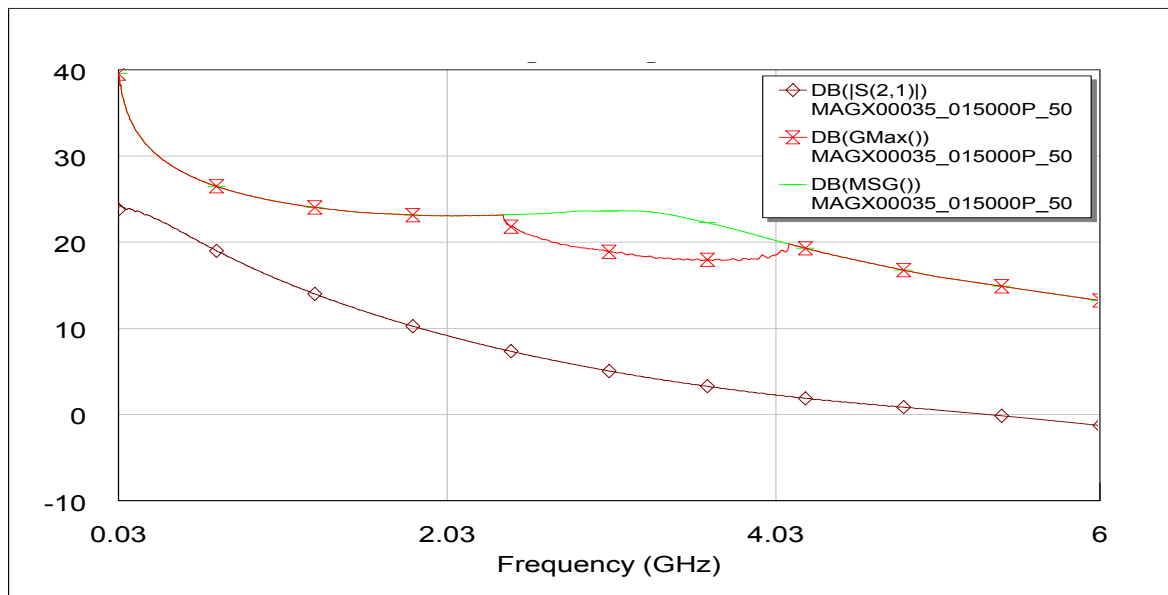
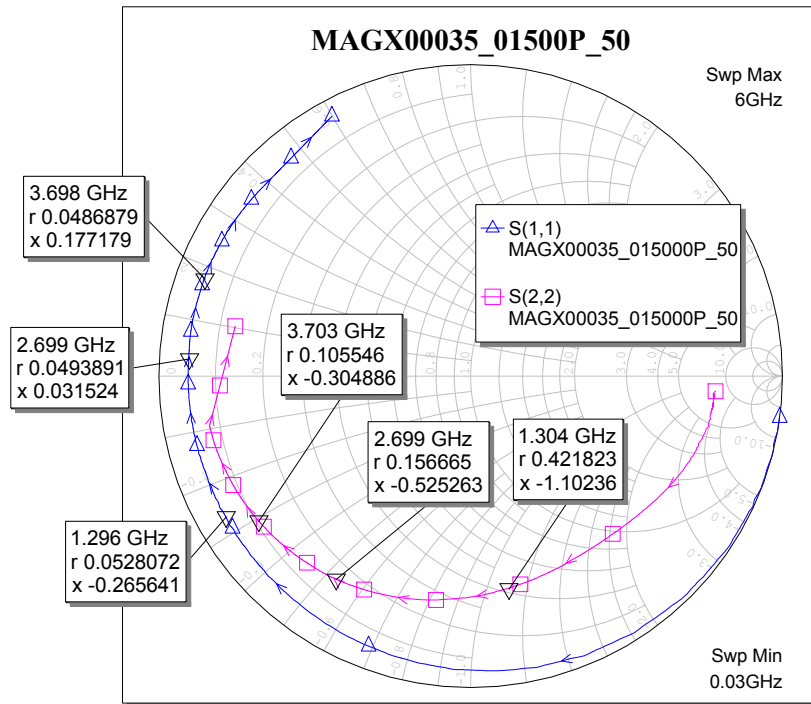
Please observe the following precautions to avoid damage:

### Static Sensitivity

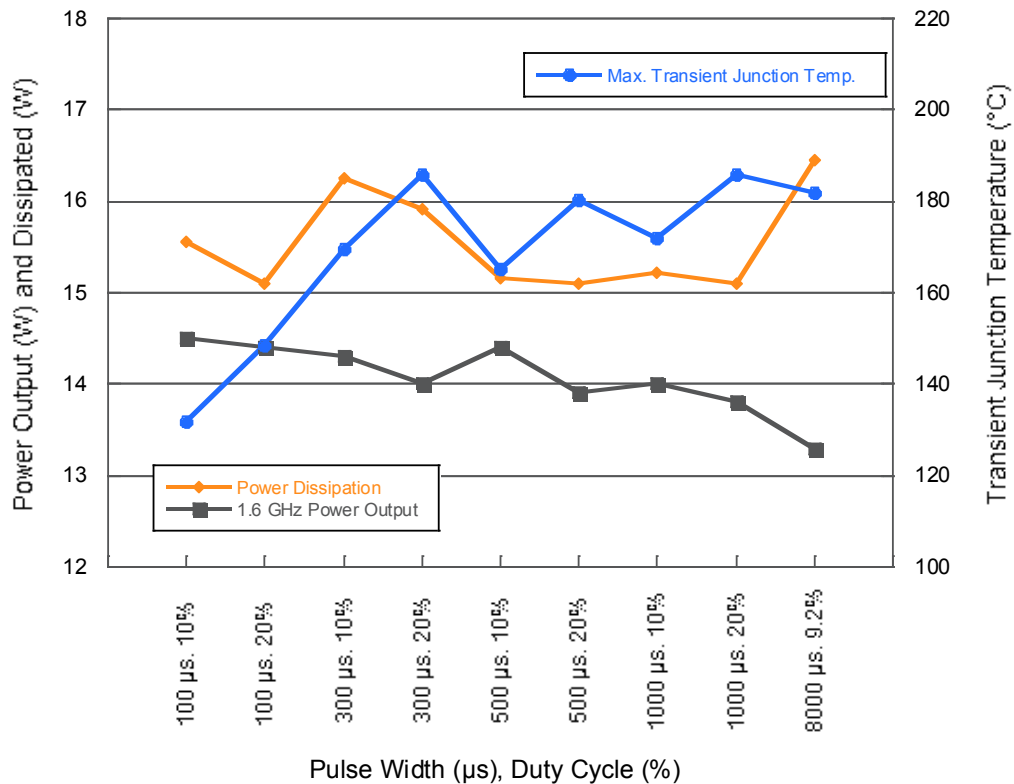
Gallium Nitride Devices and Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these Class 1B devices.

## Applications Section

S-Parameter Data:  $T_A = 25^\circ\text{C}$ ,  $V_{DD} = +50\text{ V}$ ,  $I_{DQ} = 35\text{ mA}$



## Applications Section

Thermal Performance: Freq. = 1.6 GHz,  $T_C = 85^\circ\text{C}$ ,  $V_{DD} = +50\text{ V}$ ,  $I_{DQ} = 25\text{ mA}$ ,  $Z_0 = 50\ \Omega$ **Power (Output & Dissipated) vs. Transient Junction Temperature, Pulse Duration and Duty Cycle**

Pulse Width, Duty Cycle	100 μs, 10%	100 μs, 20%	300 μs, 10%	300 μs, 20%	500 μs, 10%	500 μs, 20%	1000 μs, 10%	1000 μs, 20%	8000 μs, 9.2%
Power Dissipation (W)	15.6	15.1	16.3	15.9	15.2	15.1	15.2	15.1	16.5
1.6 GHz P <sub>OUT</sub> (W)	14.5	14.4	14.3	14	14.4	13.9	14	13.8	13.3
Max. Transient Junction Temp. (°C)	131.9	148.3	169.6	185.9	165.1	180.2	172	185.9	182

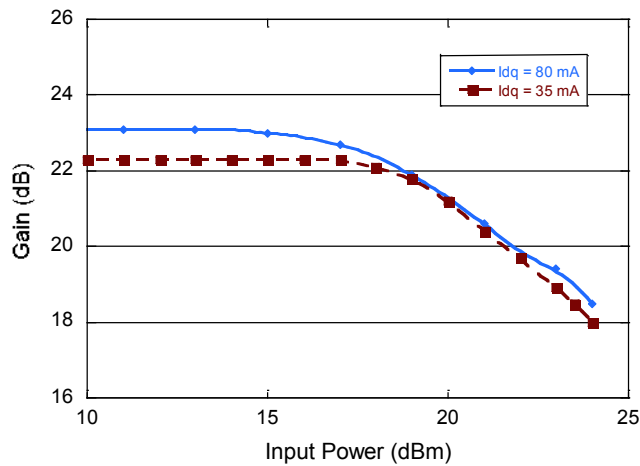
Junction temperature measured using High-Speed Transient (HST) temperature detection microscopy.

## Applications Section

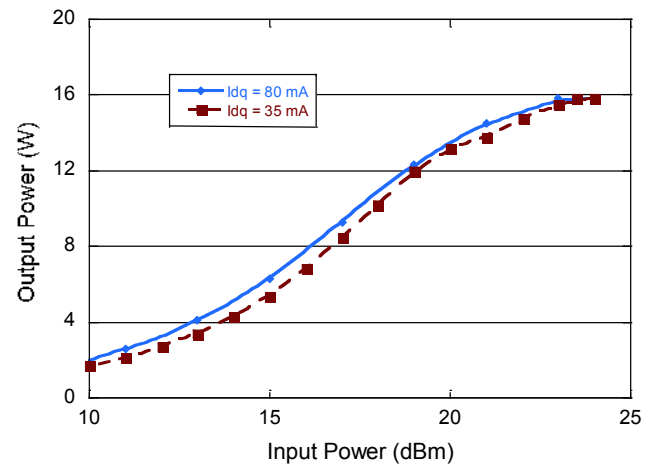
**Typical Performance Curves (reference 1.6 GHz parts list):**

**1.6 GHz, 1 ms Pulse, 10% Duty Cycle,  $V_{DD} = +50$  V,  $T_A = 25^\circ\text{C}$ ,  $Z_0 = 50\ \Omega$**

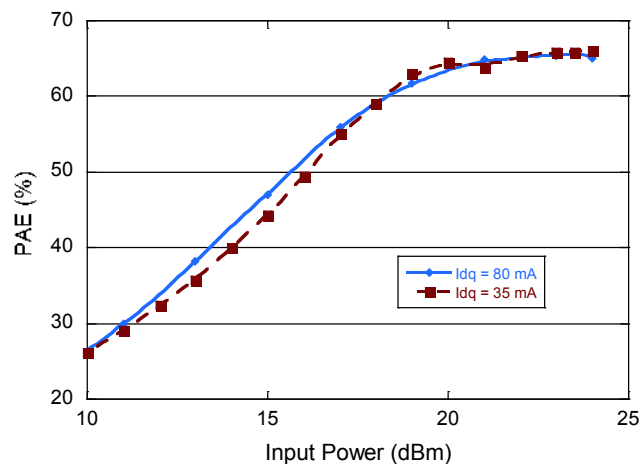
**Gain vs. Input Power**



**Output Power vs. Input Power**



**PAE vs. Input Power**





## Applications Section

### Pulsed OIP3 data

**Pulse width 8.28 ms, Duty cycle 9%**

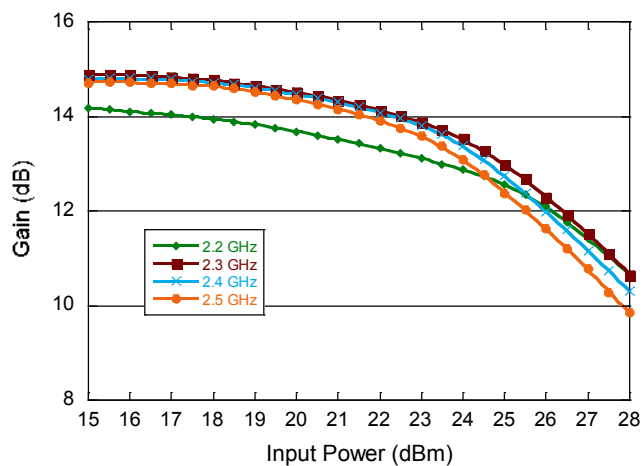
**$V_{DD} = 50 \text{ V}$ ,  $I_{DQ} = 70 \text{ mA}$ , Freq = 1.62 GHz, 1 MHz spacing on tones**

$P_{IN}$ (dBm)	$P_{OUT}$ per tone (dBm)	OIP3 (dBm)
8	31.1	46
9	32.0	47
10	32.9	50
11	33.7	50
12	34.5	47

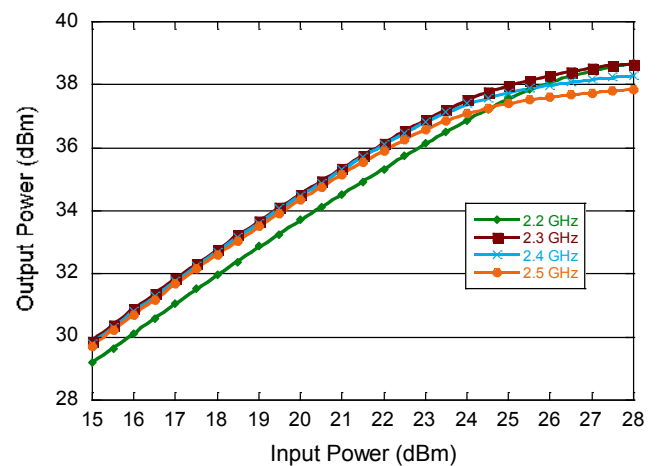
### Typical Performance Curves (reference 2.2 - 2.5 GHz parts list):

**2.2 - 2.5 GHz, CW,  $V_{DD} = 28 \text{ V}$ ,  $I_{DQ} = 35 \text{ mA}$ ,  $T_A = 25^\circ\text{C}$ ,  $Z_0 = 50 \Omega$**

**Gain vs. Input Power**



**Output Power vs. Input Power**

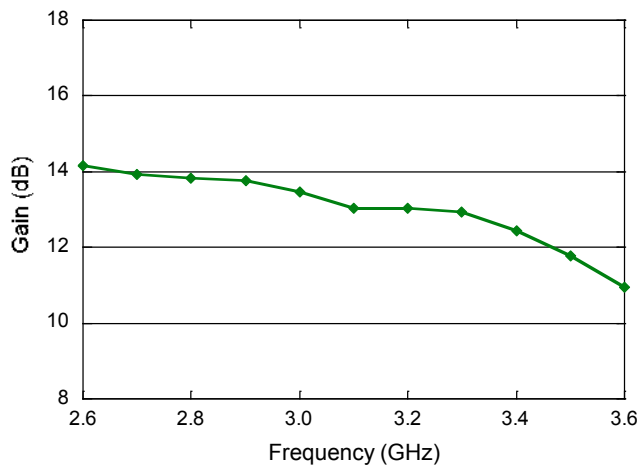


## Applications Section

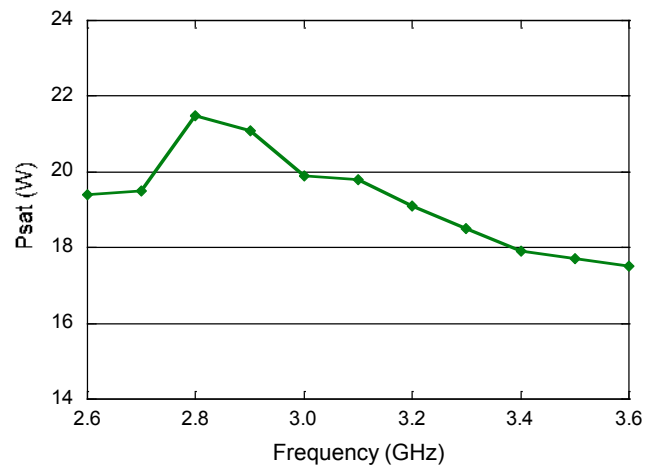
**Typical Performance Curves (reference 2.6 - 3.6 GHz parts list):**

**2.6 - 3.6 GHz, 3 ms Pulse, 10% Duty Cycle,  $V_{DD} = 50$  V,  $I_{DQ} = 35$  mA,  $T_A = 25^\circ\text{C}$ ,  $Z_0 = 50 \Omega$**

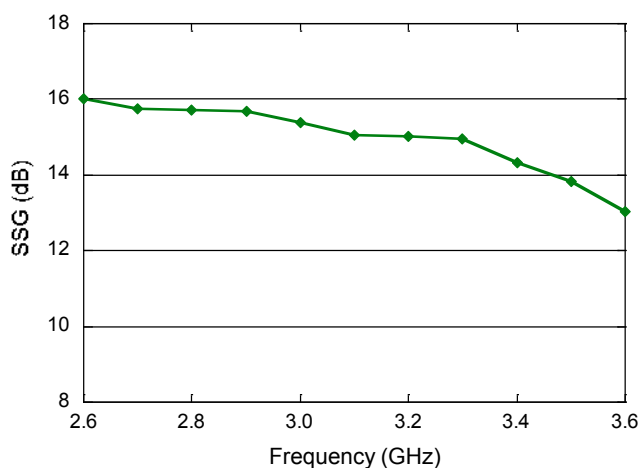
**Gain vs. Frequency**



**$P_{SAT}$  vs. Frequency**



**Small Signal Gain vs. Frequency**



**PAE vs. Frequency**

